

5V 32K X 8 CMOS SRAM (Common I/O)

Features

- Industrial (-40° to 85°C) temperature
- Organization: 32,768 words × 8 bits
- High speed
 - 15 ns address access time
 - 6 ns output enable access time
- Low power consumption via chip deselect
- One chip select plus one Output Enable pin
- Bidirectional data inputs and outputs
- TTL-compatible

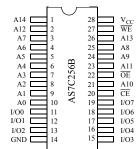
- 28-pin JEDEC standard packages
- 300 mil SOJ
- 8 × 13.4 mm TSOP
- 300 mil PDIP
- ESD protection ≥ 2000 volts

Logic block diagram

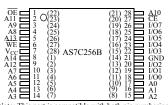
V_{CC} GND-Input buffer I/O7 A1 Address decoder A2 32,768 X 8 A3 Array Α4 (262,144) Α5 A6 I/O0 A7 WE Address decoder Control ŌE circuit CE A A A A A 10 11 12 13 14

Pin arrangement

28-pin DIP, SOJ (300 mil)



28-pin TSOP 1 (8×13.4mm)



conventions used by various manufacturers.



Functional description

The AS7C256B is a 5V high-performance CMOS 262,144-bit Static Random-Access Memory (SRAM) device organized as $32,768 \text{ words} \times 8 \text{ bits}$. It is designed for memory applications requiring fast data access at low voltage, including Pentium TM, PowerPCTM, and port able computing. All iance's advanced circuit design and process techniques permit 5.0V operation without sacrificing performance or operating margins.

The device enters *standby mode* when \overline{CE} is high. Equal address access and cycle times (t_{AA}, t_{RC}, t_{WC}) of 12 ns with output enable access times (t_{OE}) of 6 ns are ideal for high-performance applications. The chip enable (\overline{CE}) input permits easy memory expansion with multiple-bank memory organizations.

A write cycle is accomplished by asserting chip enable ($\overline{\text{CE}}$) and write enable ($\overline{\text{WE}}$) LOW. Data on the input pins I/O0-I/O7 is written on the rising edge of $\overline{\text{WE}}$ (write cycle 1) or $\overline{\text{CE}}$ (write cycle 2). To avoid bus contention, external devices should drive I/O pins only after outputs have been disabled with output enable ($\overline{\text{OE}}$) or write enable ($\overline{\text{WE}}$).

A read cycle is accomplished by asserting chip enable (\overline{CE}) and output enable (\overline{OE}) LOW, with write enable (\overline{WE}) high. The chip drives I/O pins with the data word referenced by the input address. When chip enable or output enable is high, or write enable is low, output drivers stay in high-impedance mode.

All chip inputs and outputs are TTL-compatible. Operation is from a single 5.0±0.5V supply. The AS7C256B is packaged in high volume industry standard packages.

Absolute maximum ratings

Parameter	Symbol	Min	Max	Unit			
Voltage on V _{CC} relative to GND	V _{t1}	-0.5	+7.0	V			
Voltage on any pin relative to GND	V _{t2}	-0.5	$V_{CC} + 0.5$	V			
Power dissipation	P_{D}	_	1.25	W			
Storage temperature (plastic)	T _{stg}	-55	+125	°C			
Ambient temperature with V _{CC} applied	T _{bias}	-55	+125	°C			
DC current into outputs (low)	I _{OUT}	_	50	mA			

Note:

Stresses greater than those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress ratin g only and functional operation of the device at the se or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Truth table

CE	WE	OE	Data	Mode
Н	X	X	High Z	Standby (I_{SB}, I_{SB1})
L	Н	Н	High Z	Output disable (I _{CC})
L	Н	L	D _{OUT}	Read (I _{CC})
L	L	X	$\mathrm{D_{IN}}$	Write (I _{CC})

Notes:

$$\begin{split} H &= V_{IH}, L = V_{IL}, x = Don't \ care. \\ V_{LC} &= 0.2 V, \ V_{HC} = V_{CC} - 0.2 V. \\ Other \ inputs &\geq V_{HC} \ or \ V_{LC}. \end{split}$$



Recommended operating conditions

Parameter	Symbol	Min	Typical	Max	Unit
Supply voltage	V _{CC}	4.5	5.0	5.5	V
Input voltage	V _{IH}	2.2	_	V _{CC} +0.5	V
input vottage	$V_{IL}^{(I)}$	$-0.5^{(I)}$	_	0.8	V
Ambient operating temperature (Industrial)	T _A	-40	_	85	°C

Note:

DC operating characteristics (over the operating range)¹

			AS7C2	56B-17	
Parameter	Symbol	Test conditions	Min	Max	Unit
Input leakage current	$ I_{LI} $	$V_{CC} = Max$, $V_{in} = GND \text{ to } V_{CC}$	_	5	μΑ
Output leakage current	I _{LO}	$V_{CC} = Max, \overline{CS} = V_{IH},$ $V_{OUT} = GND \text{ to } V_{CC}$	_	5	μА
Operating power supply current	I_{CC}	$V_{CC} = Max, \overline{CE} \le V_{IL}$ $f = f_{Max}, I_{OUT} = 0mA$	_	150	mA
	I_{SB}	$V_{CC} = Max, \overline{CE} \ge V_{IH}$ $f = f_{Max}, I_{OUT} = 0mA$	_	40	mA
Standby power supply current	I_{SB1}	$\begin{aligned} V_{CC} &= \text{Max, } \overline{\text{CE}} \geq V_{CC} - 0.2V \\ V_{IN} &\leq \text{GND} + 0.2V \text{ or} \\ V_{IN} &\geq V_{CC} - 0.2V, f = 0^{(2)} \end{aligned}$	_	15	mA
Output voltage	V_{OL}	$I_{OL} = 8 \text{ mA}, V_{CC} = \text{Min}$	-	0.4	V
Output voltage	V_{OH}	$I_{OH} = -4 \text{ mA}, V_{CC} = \text{Min}$	2.4	_	V

Notes:

All values are maximum guaranteed values.

 $f_{Max} = 1/t_{RC}$, only address inputs cycling at f_{Max} , f = 0 means that no inputs are cycling.

Capacitance (f = 1MHz, T_a = room temperature, V_{CC} = NOMINAL)²

Parameter	Symbol	Signals	Test conditions	Max	Unit
Input capacitance	C_{IN}	$A, \overline{CE}, \overline{WE}, \overline{OE}$	$V_{in} = 3dV$	7	pF
I/O capacitance	C _{I/O}	I/O	$V_{out} = 3dV$	7	pF

Note:

This parameter is guaranteed by device characterization, but is not production tested.

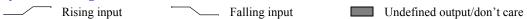
¹ V_{IL} min = -1.5V for pulse width less than 10ns, once per cycle.



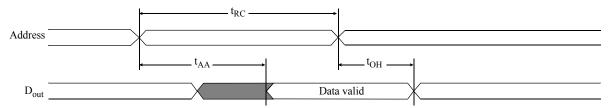
Read cycle (over the operating range)^{3,9}

		AS7C2	56B-17		
Parameter	Symbol	Min	Max	Unit	Notes
Read cycle time	t_{RC}	15	-	ns	
Address access time	t_{AA}		15	ns	3
Chip enable (\overline{CE}) access time	t _{ACE}		15	ns	3
Output enable (OE) access time	t _{OE}	-	7	ns	
Output hold from address change	t_{OH}	3	_	ns	5
CE LOW to output in low Z	t_{CLZ}	4	_	ns	4, 5
CE HIGH to output in high Z	t _{CHZ}	0	7	ns	4, 5
OE LOW to output in low Z	t_{OLZ}	0	_	ns	4, 5
OE HIGH to output in high Z	t_{OHZ}	0	6	ns	4, 5
Power up time	t_{PU}	0	_	ns	4, 5
Power down time	t _{PD}	-	15	ns	4, 5

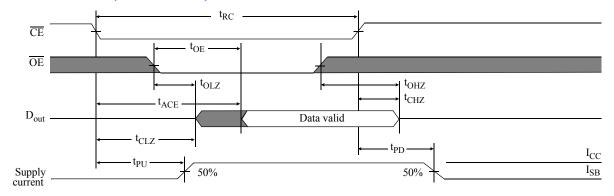
Key to switching waveforms



Read waveform 1 (address controlled)^{3,6,7,9}



Read waveform 2 (CE controlled)^{3,6,8,9}



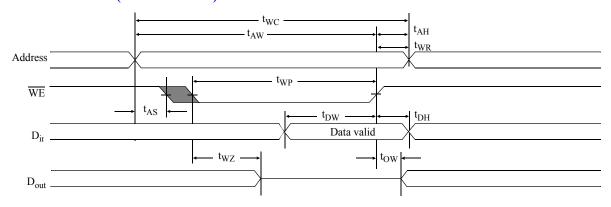


Write cycle (over the operating range) II

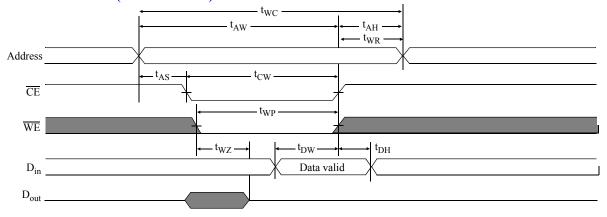
• • • • • • • • • • • • • • • • • • • •		AS7C256B-15			
Parameter	Symbol	Min	Max	Unit	Notes
Write cycle time	t_{WC}	15	_	ns	
Chip enable to write end	t _{CW}	10	_	ns	
Address setup to write end	t _{AW}	10	_	ns	
Address setup time	t _{AS}	0	_	ns	
Write pulse width	t _{WP}	10	-	ns	
Write recovery time	t _{WR}	0	_	ns	
Address hold from end of write	t _{AH}	0	_	ns	
Data valid to write end	$t_{\rm DW}$	7	_	ns	
Data hold time	t _{DH}	0	_	ns	4, 5
Write enable to output in high Z	t_{WZ}	0	6	ns	4, 5
Output active from write end	t _{OW}	4	-	ns	4, 5

Shaded areas contain advance information.

Write waveform 1 (WE controlled)^{10,11}



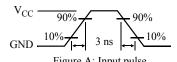
Write waveform 2 ($\overline{\text{CE}}$ controlled)^{10,11}





AC test conditions

- Output load: see Figure B.
- Input pulse level: GND to V_{CC} . See Figure A.
- Input rise and fall times: 3 ns. See Figure A.
- Input and output timing reference levels: 1.5V.



Thevenin equivalent

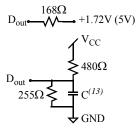


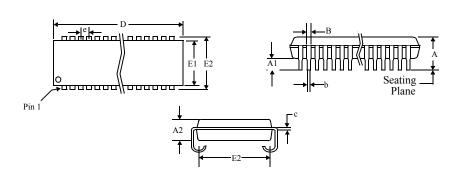
Figure B: Output load

Notes

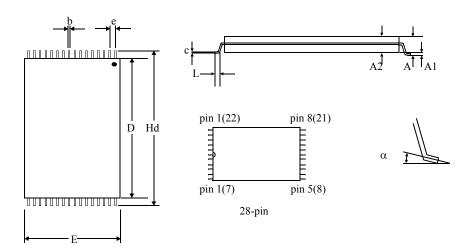
- 1 During V_{CC} power-up, a pull-up resistor to V_{CC} on \overline{CE} is required to meet I_{SB} specification.
- 2 This parameter is sampled, but not 100% tested.
- 3 For test conditions, see AC Test Conditions, Figures A and B.
- $4 \quad \text{These parameters are specified with CL} = 5 pF, as in Figures B. Transition is measured \pm 200 mV from steady-state voltage.}$
- 5 This parameter is guaranteed, but not tested.
- $\overline{\text{WE}}$ is High for read cycle.
- 7 $\overline{\text{CE}}$ and $\overline{\text{OE}}$ are Low for read cycle.
- 8 Address valid prior to or coincident with $\overline{\text{CE}}$ transition Low.
- 9 All read cycle timings are referenced from the last valid address to the first transitioning address.
- 10 $\overline{\text{CE}}$ or $\overline{\text{WE}}$ must be High during address transitions. Either $\overline{\text{CE}}$ or $\overline{\text{WE}}$ asserting high terminates a write cycle.
- 11 All write cycle timings are referenced from the last valid address to the first transitioning address.
- 12 \overline{CE1} and CE2 have identical timing.
- 13 C=30pF, except on High Z and Low Z parameters, where C=5pF.



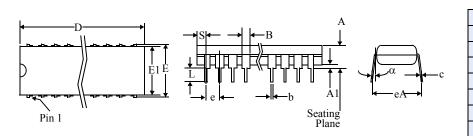
Package diagrams



	28-pii	ı SOJ	
	Min	Max	
	in r	nils	
A	1	0.140	
A1	0.025	1	
A2	0.095	0.105	
В	0.028 TYP		
b	0.018	TYP	
c	0.010	TYP	
D	1	0.730	
E	0.245	0.285	
E 1	0.295	0.305	
E2	0.327	0.347	
e	0.050	BSC	



ı				
	28-pin			
	8×13.4 mm			
	Min	Max		
A	ı	1.20		
A1	0.10	0.20		
A2	0.95	1.05		
b	0.15	0.25		
c	0.10	0.20		
D	11.60	11.80		
e	0.55 n	ominal		
E	8.0 nc	minal		
Hd	13.30	13.50		
L	0.50	0.70		
α	0°	5°		



Note: This part is compatible with both pin numbering conventions used by various manufacturers.

	28-pin	PDIP
	Min	Max
	in r	nils
A	-	0.180
A1	0.010	-
В	0.040	0.065
b	0.014	0.022
c	0.008	0.014
D	-	1.400
E	0.295	0.320
E1	0.278	0.298
e	0.100	BSC
eA	0.330	0.380
L	0.120	0.140
a	0°	15°
S	-	0.055



Ordering information

Package	Volt/Temp	12 ns
Plastic DIP, 300 mil	5V industrial	AS7C256B-12PIN
Plastic SOJ, 300 mil	5V industrial	AS7C256B-15JIN
TSOP 8x13.4 mm	5V industrial	AS7C256B-12TIN

Part numbering system

AS7C	256B	-XX	X	I	X
SRAM prefix	Device number	Access time	Package: P=DIP 300 mil J=SOJ 300 mil T=TSOP 8x13.4 mm	Temperature range: I = -40C to 85C	N=Lead Free Part



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